

# **MAS6180B**

## **AM Receiver IC**

- Single Band Receiver IC
- High Sensitivity
- Very Low Power Consumption
- Wide Supply Voltage Range
- Power Down Control
- Control for AGC On
- High Selectivity by Crystal Filter
- Fast Startup Feature

#### **DESCRIPTION**

The MAS6180 AM-Receiver chip is a highly sensitive, simple to use AM receiver specially intended to receive time signals in the frequency range from 40 kHz to 100 kHz. Only a few external components are required for time signal receiver. The circuit has preamplifier, wide range automatic gain control, demodulator and output comparator built in. The output signal can be processed directly by an additional digital circuitry to extract the

data from the received signal. The control for AGC (automatic gain control) can be used to switch AGC on or off if necessary.

MAS6180 has two options for compensating shunt capacitances of different crystals (See ordering information on page 13).

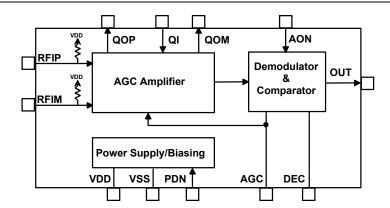
#### **FEATURES**

- Single Band Receiver IC
- Highly Sensitive AM Receiver
- Wide Supply Voltage Range from 1.1 V to 3.6 V
- Very Low Power Consumption
- Power Down Control
- Fast Startup
- Only a Few External Components Necessary
- Control for AGC On
- Wide Frequency Range from 40 kHz to 100 kHz
- High Selectivity by Quartz Crystal Filter
- Crystal Compensation Capacitance Options
- Differential Input

#### **APPLICATIONS**

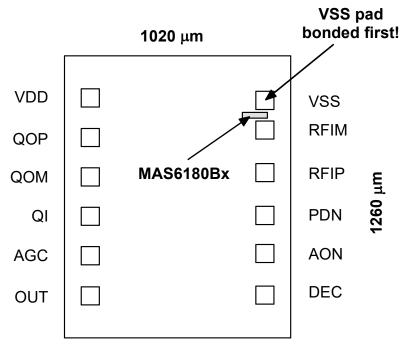
 Single Band Time Signal Receiver WWVB (USA), JJY (Japan), DCF77 (Germany), MSF (UK), HBG (Switzerland) and BPC (China)

#### **BLOCK DIAGRAM**





### **MAS6180 PAD LAYOUT**



DIE size =  $1020 \mu m \ x \ 1260 \mu m$ ; PAD size =  $80 \mu m \ x \ 80 \mu m$ 

**Note:** Because the substrate of the die is internally connected to VSS, the die has to be connected to VSS or left floating. Please make sure that VSS is the first pad to be bonded. Pick-and-place and all component assembly are recommended to be performed in ESD protected area.

**Note:** Coordinates are pad center points where origin has been located in bottom-left corner of the silicon die.

Pad Identification	Name	X-coordinate	Y-coordinate	Note
Power Supply Voltage	VDD	126 μm	1062 μm	
Positive Quartz Filter Output for Crystal	QOP	126 μm	893 μm	
Negative Quartz Filter Output for Crystal	QOM	126 μm	723 μm	1
Quartz Filter Input for Crystal and External Compensation Capacitor	QI	126 μm	549 μm	
AGC Capacitor	AGC	126 μm	375 μm	
Receiver Output	OUT	126 μm	198 μm	2
Demodulator Capacitor	DEC	894 μm	201 μm	
AGC On Control	AON	894 μm	385 μm	3
Power Down	PDN	894 μm	553 μm	4
Positive Receiver Input	RFIP	894 μm	742 μm	5
Negative Receiver Input	RFIM	894 μm	920 μm	5
Power Supply Ground	VSS	894 μm	1051 μm	

#### Notes:

- 1) External crystal compensation capacitor pin QOM is connected only in MAS6180B5 version. It is left unconnected in MAS6180B1 version which has internal compensation capacitor.
- 2) OUT = VSS when carrier amplitude at maximum; OUT = VDD when carrier amplitude is reduced (modulated)
  - The output is a current source/sink with |I<sub>OUT</sub>| > 5 μA
  - At power down the output is pulled to VSS (pull down switch)
- 3) AON = VSS means AGC off (hold current gain level); AON = VDD means AGC on (normal operation)
  - Unused AON pad can be left unconnected due to internal pull-up with current < 1  $\mu$ A. Pull up current is switched off at power down.
- 4) PDN = VSS means receiver on; PDN = VDD means receiver off
  - Fast start-up is triggered when the receiver is after power down (PDN=VDD) controlled to power up (PDN=VSS) i.e. at the falling edge of PDN signal.
- 5) Receiver inputs RFIP and RFIM have both 1.4 M $\Omega$  biasing resistors towards VDD



## **ABSOLUTE MAXIMUM RATINGS**

All Voltages with Respect to Ground

Parameter	Symbol	Conditions	Min	Max	Unit
Supply Voltage	V <sub>DD</sub> -V <sub>SS</sub>		- 0.3	3.6	V
Input Voltage	Vin		Vss-0.3	V <sub>DD</sub> +0.3	V
Operating Temperature	T <sub>OP</sub>		-40	+85	°C
Storage Temperature	Tst		- 55	+150	°C

**Note:** Stresses beyond those listed may cause permanent damage to the device. The device may not operate under these conditions, but it will not be destroyed.

Note: This is a CMOS device and therefore it should be handled carefully to avoid any damage by static voltages (ESD).

## **ELECTRICAL CHARACTERISTICS**

ParameterSymbolConditionsMinTypMaxUnitOperating Voltage $V_{DD}$ 1.11.53.6VCurrent Consumption $I_{DD}$ VDD=1.5 V, Vin=0 μVrms<br/>VDD=1.5 V, Vin=20 mVrms<br/>4066<br/>40μA

Operating Conditions: VDD = 1.5V, Temperature = 27°C, unless otherwise specified.

Operating voltage	<b>V</b> DD		1.1	1.5	5.0	V
Current Consumption	I <sub>DD</sub>	VDD=1.5 V, Vin=0 μVrms VDD=1.5 V, Vin=20 mVrms		66 40		μА
		VDD=3.6 V, Vin=0 μVrms	31	68	85	
		VDD=3.6 V, Vin=20 mVrms	24	42	65	
Stand-By Current	I <sub>DDoff</sub>	See note below.			0.1	μΑ
Input Frequency Range	f <sub>IN</sub>		40		100	kHz
Minimum Input Voltage	V <sub>IN min</sub>			0.4	1	μVrms
Maximum Input Voltage	V <sub>IN max</sub>		20			mVrms
Receiver Input Resistance	R <sub>RFI</sub>	Differential Input,		600		kΩ
Receiver Input Capacitance	C <sub>RFI</sub>	f=40 kHz77.5 kHz		1.1		pF
Input Levels  I <sub>IN</sub>  <0.5 μA	VIL				0.35	V
input Levels  iiiv  10.5 μΑ	VIH		V <sub>DD</sub> -		0.00	ŭ
	• ""		0.35			
Output Current	Поит		5			μΑ
$V_{OL} < 0.2 V_{DD}; V_{OH} > 0.8 V_{DD}$						•
DCF77 Output Pulses	T <sub>100ms</sub>	1 μVrms ≤ V <sub>IN</sub> ≤		95		ms
	T <sub>200ms</sub>	20 mVrms, see note below!		195		
MSF Output Pulses	T 100ms	1 $\mu$ Vrms $\leq$ V <sub>IN</sub> $\leq$		120		ms
	T 200ms	20 mVrms, see note below!		220		
	T 300ms			320		
MAAAAD Oostaast Dallaga	T 500ms	4 1/22 (1)		520		
WWVB Output Pulses	T <sub>200ms</sub>	$1 \mu Vrms \le V_{IN} \le$		200 500		ms
	T <sub>500ms</sub>	20 mVrms, see note below!		800		
JJY60 Output Pulses	T 200ms	1 μVrms ≤ V <sub>IN</sub> ≤		210		ms
or to output i diece	T 500ms	20 mVrms, see note below!		505		1110
	T 800ms			800		
JJY40 Output Pulses	T <sub>200ms</sub>	1 μVrms ≤ V <sub>IN</sub> ≤		200		ms
	T <sub>500ms</sub>	20 mVrms, see note below!		495		
	T <sub>800ms</sub>			790		
Startup Time	T <sub>Start</sub>	Fast Start-up, Vin=0.4 μVrms		1.3		S
		Fast Start-up, Vin=20 mVrms		3.5		
Output Delay Time	T <sub>Delay</sub>			50	100	ms

Note: Stand-by current consumption may increase if V  $_{\rm IH}$  and V  $_{\rm IL}$  differ from VDD and 0 respectively. Note: See Note 6: Time Signal Software's Pulse Width Recognition Limits and Table 5 on page 8!



## **TYPICAL APPLICATION**

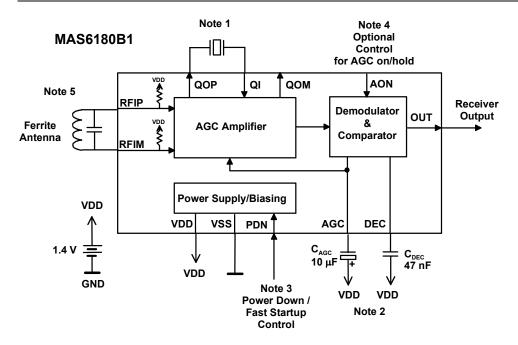


Figure 1. Application circuit of internal compensation capacitance option version MAS6180B1.

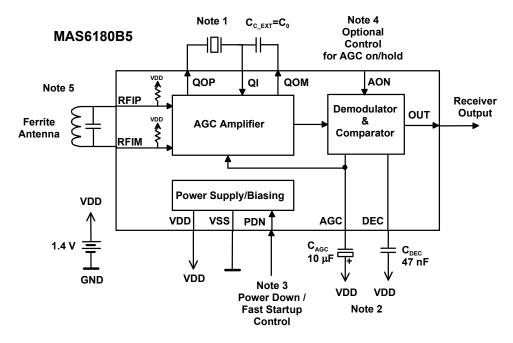
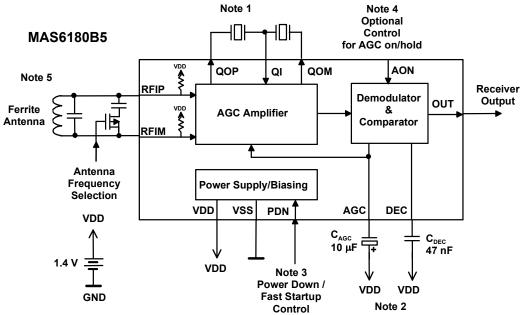


Figure 2. Application circuit of external compensation capacitance option version MAS6180B5.





**Figure 3.** Dual band application circuit of external compensation capacitance option version MAS6180B5. PMOS switch transistor is used since RFIM input is biased close to VDD voltage.



#### Note 1: Crystals

The crystal as well as ferrite antenna frequencies are chosen according to the time-signal system (Table 1). More detailed crystal nominal frequency is normally specified for certain load capacitance but in MAS6180 filter circuit the load capacitance is not used. Effectively this means that most accurate filter frequency is achieved by using about 3 Hz higher frequency crystal than the received time signal frequency. For example in DCF77 application a 77.503 kHz crystal resonates at the desired DCF77 77.500 kHz frequency when the load capacitor is missing.

Table 1. Time-Signal System Frequencies

Time-Signal System	Location	Antenna Frequency	Recommended Crystal Frequency
DCF77	Germany	77.5 kHz	77.503 kHz
HBG	Switzerland	75 kHz	75.003 kHz
MSF	United Kingdom	60 kHz	60.003 kHz
WWVB	USA	60 kHz	60.003 kHz
JJY	Japan	40 kHz and 60 kHz	40.003 kHz and 60.003 kHz
BPC	China	68.5 kHz	68.505 kHz

The crystal shunt capacitance  $C_0$  should be matched as well as possible with the internal shunt capacitance compensation capacitor  $C_0$  of MAS6180. MAS6180B5 is option for external crystal compensation capacitor. The external compensation capacitor should be matched similarly as well as possible with crystal's shunt capacitance. See Compensation Capacitance Options on table 2.

Table 2. Compensation Capacitance Options

Device	Cc	Crystal Description			
MAS6180B1	0.75 pF	For low C <sub>0</sub> crystals			
MAS6180B5	C <sub>C EXT</sub>	For any crystals, external compensation capacitor			

It should be noted that grounded crystal package has reduced shunt capacitance. This value is about 85% of floating crystal shunt capacitance. For example crystal with 1 pF floating package shunt capacitance can have 0.85 pF grounded package shunt capacitance. PCB traces of crystal and external compensation capacitance should be kept at minimum to minimize additional parasitic capacitance which can cause capacitance mismatching.

In dual band receiver configuration the crystals are best to connect as shown in figure 3. In this configuration the crystals' shunt capacitances compensate each other and external compensation capacitor is not needed at all.

Table 3 below presents some crystal suppliers having suitable crystals for time signal receiver application.

Table 3. Crystal Suppliers and Crystal Types in Alphabetical Order for Time Signal Receiver Application

Supplier	Crystal Type	Dimensions	Web Link
Citizen	CFV-206	ø 2.0 x 6.0	http://www.citizen.co.jp/tokuhan/quartz/
Epson Toyocom	C-2-Type	ø 1.5 x 5.0	http://www.epsontoyocom.co.jp/english/
	C-4-Type	ø 2.0 x 6.0	
KDS Daishinku	DT-261	ø 2.0 x 6.0	http://www.kds.info/index_en.htm
Microcrystal	MS3V-T1R	1.45 x 1.45 x 6.7	http://www.microcrystal.com/
Seiko	VTC-120	ø 1.2 x 4.7	http://www.sii-crystal.com
Instruments			



#### **Note 2: AGC Capacitor**

The AGC and DEC capacitors must have low leakage currents due to very small signal currents through the capacitors. The insulation resistance of these capacitors should be at minimum 100 M $\Omega$ . Also probes with at least few 100 M $\Omega$  impedance should be used for voltage probing of the AGC and DEC pins. Electrolytic AGC capacitor should have voltage rating at least 25 V for low enough leakage. DEC capacitor can be low leakage chip capacitor. It is recommended to connect both AGC and DEC capacitors to VDD (see application figures 1, 2 and 3) although VSS connection is also possible. The VDD connection provides better supply noise immunity because signals are referenced to VDD. Additionally leakage currents are minimized in this connection because in power down the AGC pin voltage is pulled to VDD (to minimum AGC gain) then corresponding to zero voltage over the AGC capacitor.

#### Note 3: Power Down / Fast Startup Control

Both power down and fast startup are controlled using the PDN pin. The device is in power down (turned off) if PDN = VDD and in power up (turned on) if PDN = VSS. Fast startup is triggered automatically by the falling edge of PDN signal, i.e., controlling device from power down to power up. The VDD must be high before falling edge of PDN to guarantee proper operation of fast startup circuitry. Before power up the device should have been kept in power down state at least 50ms. This guarantees that the AGC capacitor voltage has been completely pulled to VDD during power down. The startup time without proper fast startup control can be over minute but with fast startup it is shortened typically to a few seconds.

#### Note 4: Optional Control for AGC On/Hold

AON control pin has internal pull up which turns AGC circuit on all the time if AON pin is left unconnected. Optionally AON control can be used to hold and release AGC circuit. Stepper motor drive of analog clock or watch can produce disturbing amount of noise which can shift the input amplifier gain to unoptimal level. This can be avoided by controlling AGC hold (AON=VSS) during stepper motor drive periods and releasing AGC (AON=VDD) when motors are not driven. The AGC should be in hold only during disturbances and kept on other time released since due to leakage the AGC voltage can change slowly even when in hold.

#### Note 5: Ferrite Antenna

The ferrite antenna converts the transmitted radio wave into a voltage signal. It has an important role in determining receiver performance. Recommended antenna impedance at resonance is around 100 k $\Omega$ .

Low antenna impedance corresponds to low noise but often also to small signal amplitude. On the other hand high antenna impedance corresponds to high noise but also large signal. The optimum performance where signal-to-noise ratio is at maximum is achieved in between.

The antenna should have also some selectivity for rejecting near signal band disturbances. This is determined by the antenna quality factor which should be approximately 100. Much higher quality factor antennas suffer from extensive tuning accuracy requirements and possible tuning drifts by the temperature.

Antenna impedance  $R_{ant}$  can be calculated using equation 1 where  $f_{res}$ , L,  $Q_{ant}$  and C are resonance frequency, coil inductance, antenna quality factor and antenna tuning capacitor respectively. Antenna quality factor  $Q_{ant}$  is defined by ratio of resonance frequency  $f_{res}$  and antenna bandwidth B (equation 2).

$$R_{ant} = 2\pi \cdot f_{res} \cdot L \cdot Q_{ant} = \frac{Q_{ant}}{2\pi \cdot f_{res} \cdot C} = \frac{1}{2\pi \cdot B \cdot C}$$
 Equation 1.

$$Q_{ant} = \frac{f_{res}}{R}$$
 Equation 2.

Table 4 on next page presents some antenna suppliers for time signal application.



Table 4. Antenna Suppliers and Antenna Types for Time Signal Application

Supplier	Antenna Type	Dimensions	Web Link
Micro Analog	A10X60-77.5K222PY	ø 10 x 60 mm	http://www.mas-
Systems Oy	A10X100-77.5K222PY	ø 10 x 100 mm	oy.com/en/products/radio-controlled-
	A3.5X4X15-7.87MH	3.5 x 4 x 15 mm	clock-rcc/antennas/
	A2X3X21-0.92MH	2 x 3 x 21 mm	
	A3.75X3.75X23.6-0.92MH	3.75x3.75x23 mm	
HR Electronic	60716 (60 kHz)	ø 10 x 60 mm	http://www.hrelectronic.com/
GmbH	60708 (77.5 kHz)		
Hitachi Metals	AN-T702Sxx	19 x 5.5 x 6.3 mm	http://www.hitachi-
	AN-T702Mxx	28 x 5 x 5 mm	metals.co.jp/e/prod/prod06/p06 12.html
	AN-T702Lxx	50 x 5 x 5 mm	
Premo	RCA-SMD-77A (77.5 kHz)	75 x 15 x 6.3 mm	http://www.grupopremo.com/
	RCA-SMD-60A (60 kHz)		
Sumida	ACL80A (40 kHz)	ø 10 x 80 mm	www.sumida.co.jp/jeita/XJA021.pdf

#### Note 6: Time Signal Software's Pulse Width Recognition Limits

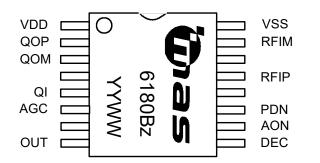
The typical output pulse width specifications are presented in the electrical characteristics section on page 3. Due to process variations the typical output pulse width can differ from these. Additionally the output pulse widths can vary even more depending on the receiving antenna signal strength versus noise and disturbance conditions. That is why it is important that the time signal decoding software has appropriate tolerance limits for managing the output pulse width variations successfully. The table 5 presents recommended software pulse width tolerance limits for recognizing pulses of different time signals.

Table 5. Recommended Software Pulse Width Recognition Limits for Different Time Signals

Parameter	Symbol	Min	Max	Unit
DCF77 Output Pulses	T <sub>100ms</sub>	40	130	ms
	T <sub>200ms</sub>	140	250	
MSF Output Pulses	T <sub>100ms</sub>	50	160	ms
	T <sub>200ms</sub>	170	270	
	T <sub>300ms</sub>	280	380	
	T <sub>500ms</sub>	400	600	
WWVB Output Pulses	T <sub>200ms</sub>	100	300	ms
	T <sub>500ms</sub>	400	600	
	T <sub>800ms</sub>	700	900	
JJY60 Output Pulses	T <sub>200ms</sub>	100	300	ms
	T <sub>500ms</sub>	400	600	
	T 800ms	700	900	
JJY40 Output Pulses	T <sub>200ms</sub>	100	300	ms
	T <sub>500ms</sub>	400	600	
	T 800ms	700	900	



#### PIN CONFIGURATION & TOP MARKING FOR PLASTIC TSSOP-16 PACKAGE



Top Marking Definitions: z = Version Number YYWW = Year Week

#### PIN DESCRIPTION

Pin Name	Pin	Туре	Function	Note
VDD	1	Р	Positive Power Supply	
QOP	2	AO	Positive Quartz Filter Output for Crystal	
QOM	3	AO	Negative Quartz Filter Output for External Compensation Capacitor or Second Crystal	1
	4	NC		2
QI	5	Al	Quartz Filter Input for Crystal and External Compensation Capacitor	
AGC	6	AO	AGC Capacitor	
	7	NC		2
OUT	8	DO	Receiver Output	3
DEC	9	AO	Demodulator Capacitor	
AON	10	DI	AGC On Control	4
PDN	11	DI	Power Down Input	5
	12	NC		2
RFIP	13	Al	Positive Receiver Input	6
	14	NC	2	
RFIM	15	Al	Negative Receiver Input 6	
VSS	16	G	Power Supply Ground	

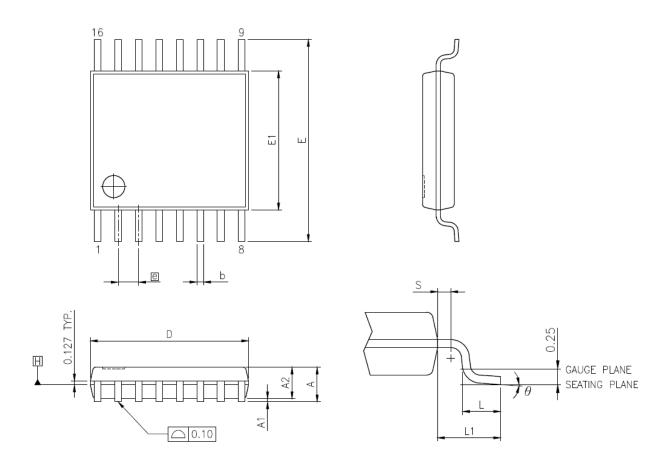
A = Analog, D = Digital, P = Power, G = Ground, I = Input, O = Output, NC = Not Connected

#### Notes:

- 1) External crystal compensation capacitor pin QOM is connected only in MAS6180B5 version. It is left unconnected in MAS6180B1 version which has internal compensation capacitor.
- 2) Pin 4 between QOM and QI must be connected to IC's filtered VDD (pin 1) to eliminate TSSOP package lead frame parasitic capacitances disturbing the crystal filter performance and minimizing noise coupling. All other NC (Not Connected) type pins are recommended to be connected to VSS.
- 3) OUT = VSS when carrier amplitude at maximum; OUT = VDD when carrier amplitude is reduced (modulated)
  - the output is a current source/sink with  $|I_{OUT}| > 5 \mu A$
  - at power down the output is pulled to VSS (pull down switch)
- 4) AON = VSS means AGC off (hold current gain level); AON = VDD means AGC on (working)
  - Internal pull-up with current < 1  $\mu$ A which is switched off at power down
- 5) PDN = VSS means receiver on; PDN = VDD means receiver off
  - Fast start-up is triggered when the receiver is after power down (PDN=VDD) controlled to power up (PDN=VSS) i.e. at the falling edge of PDN signal.
- 6) Receiver inputs RFIP and RFIM have both 1.4  $M\Omega$  biasing resistors towards VDD



## **PACKAGE (TSSOP-16) OUTLINES**



Dimension	Min	Nom	Max	Unit	
Α			1.2	mm	
A1	0.05		0.15	mm	
A2	0.80	1.00	1.05	mm	
b	0.19		0.30	mm	
D	4.90	5.00	5.10	mm	
E1	4.30	4.40	4.50	mm	
E		mm			
е		0.65 BSC			
L1		1.00 REF			
Ĺ	0.45	0.60	0.75	mm	
S	0.20			mm	
θ	0		8	0	

Dimensions do not include mold flash, protrusions, or gate burrs. All dimensions are in accordance with JEDEC standard MO-153.

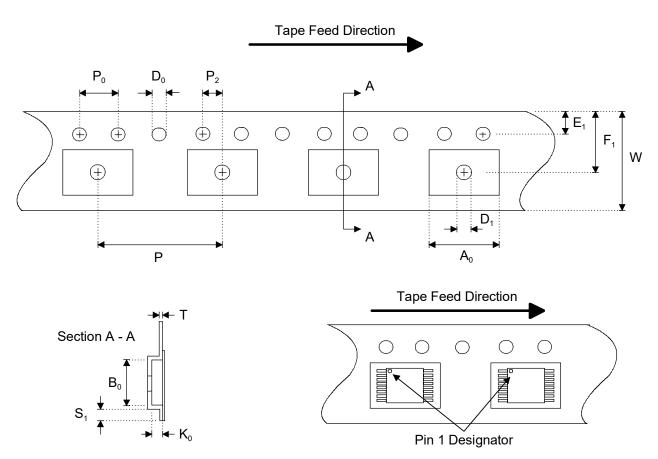


## **SOLDERING INFORMATION**

## ♦ For Pb-Free, RoHS Compliant TSSOP-16

Resistance to Soldering Heat	According to RSH test IEC 68-2-58/20
Maximum Temperature	260°C
Maximum Number of Reflow Cycles	3
Reflow profile	Thermal profile parameters stated in IPC/JEDEC J-STD-020
	should not be exceeded. <a href="http://www.jedec.org">http://www.jedec.org</a>
Seating Plane Co-planarity	max 0.08 mm
Lead Finish	Solder plate 7.62 - 25.4 µm, material Matte Tin

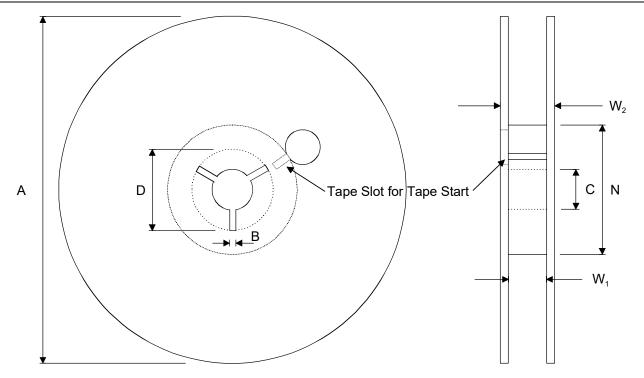
## **EMBOSSED TAPE SPECIFICATIONS**



Dimension	Min	Max	Unit
$A_0$	6.50	6.70	mm
B <sub>0</sub>	5.20	5.40	mm
D <sub>0</sub>	1.50 +0.7	10 / -0.00	mm
D <sub>1</sub>	1.50		mm
E <sub>1</sub>	1.65	1.85	mm
F <sub>1</sub>	7.20	7.30	mm
<b>K</b> <sub>0</sub>	1.20	1.40	mm
Р	11.90	12.10	mm
P <sub>0</sub>	4	.0	mm
P <sub>2</sub>	1.95	2.05	mm
S <sub>1</sub>	0.6		mm
Т	0.25	0.35	mm
W	11.70	12.30	mm

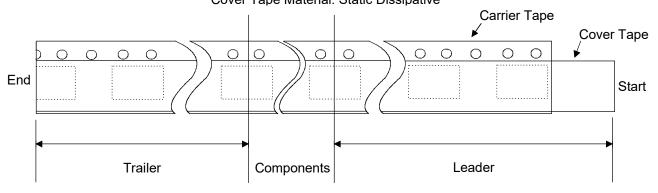


## **REEL SPECIFICATIONS**



2000 Components on Each Reel

Reel Material: Conductive, Plastic Antistatic or Static Dissipative Carrier Tape Material: Conductive Cover Tape Material: Static Dissipative



Dimension	Min	Max	Unit
Α		330	mm
В	1.5		mm
С	12.80	13.50	mm
D	20.2		mm
N	50		mm
W <sub>1</sub>	12.4	14.4	mm
(measured at hub)			
$W_2$		18.4	mm
(measured at hub)			
Trailer	160		mm
Leader	390, of which minimum 160 mm of empty carrier tape sealed with cover tape		mm
Weight		1500	g



#### ORDERING INFORMATION

Product Code	Product	Description	Capacitance Option
MAS6180B1TC00	Single Band AM-Receiver IC with Differential Input	Tested wafer with inking, diameter 8", thickness 395 µm ± 5%.	Cc = 0.75 pF
MAS6180B1TC13	Single Band AM-Receiver IC with Differential Input	Tested non-inked wafer with wafer map, diameter 8", thickness 395 µm ± 5%.	C <sub>C</sub> = 0.75 pF
MAS6180B5TC00	Single Band AM-Receiver IC with Differential Input	Tested wafer with inking, diameter 8", thickness 395 µm ± 5%.	External compensation capacitor
MAS6180B5TC13	Single Band AM-Receiver IC with Differential Input	Tested non-inked wafer with wafer map, diameter 8", thickness 395 µm ± 5%.	External compensation capacitor
MAS6180B1UC06	Single Band AM-Receiver IC with Differential Input	TSSOP-16, Pb-free, RoHS compliant, Tape & Reel	C <sub>C</sub> = 0.75 pF

Contact Micro Analog Systems Oy for other wafer thickness options.

#### **♦** The formation of product code

An example for MAS6180B1TC00:

 ur example for the Go food frood.				
MAS6180	В	1	TC	00
Product	Design	Capacitance option:	Package type:	Delivery format:
name	version	$C_C = 0.75 \text{ pF}$	TC = 400 μm thick	00 = wafer with inking
			tested wafer	05 = dies on tray
				06 = tape & reel
				08 = in tube
				13 = non-inked wafer with wafer map

OCAL DISTRIBUTOR			

## MICRO ANALOG SYSTEMS OY CONTACTS

Micro Analog Systems Oy	Tel. +358 10 835 1100
Kutomotie 16	
FI-0038 Helsinki, FINLAND	http://www.mas-oy.com

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